SamHop Microelectronics Corp.

STU/D20N15

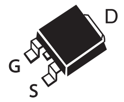
Ver 1.0

N-Channel Logic Level Enhancement Mode Field Effect Transistor

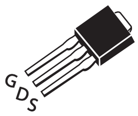
PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (mΩ) Typ
150V	20A	58 @ VGS=10V
		65 @ VGS=4.5V

FEATURES

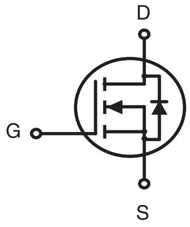
- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- TO-252 and TO-251 Package.



STU SERIES
TO-252AA(D-PAK)



STD SERIES
TO-251(I-PAK)



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		150	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Drain Current-Continuous	T_C=25°C	20	A
		T_C=70°C	16.8	A
I_{DM}	-Pulsed [a]		59	A
E_{AS}	Single Pulse Avalanche Energy [c]		0.211	mJ
P_D	Maximum Power Dissipation	T_C=25°C	50	W
		T_C=70°C	35	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		-55 to 175	°C

THERMAL CHARACTERISTICS

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	150			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=120V , V_{GS}=0V			1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V , V_{DS}=0V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=250uA	2	2.4	4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V , I_D=10A		58	73	m ohm
		V_{GS}=4.5V , I_D=9A		65	88	m ohm
g_{FS}	Forward Transconductance	V_{DS}=10V , I_D=10A		39		S
DYNAMIC CHARACTERISTICS [b]						
C_{ISS}	Input Capacitance	V_{DS}=25V,V_{GS}=0V f=1.0MHz		4700		pF
C_{OSS}	Output Capacitance			157		pF
C_{RSS}	Reverse Transfer Capacitance			122		pF
SWITCHING CHARACTERISTICS [b]						
$t_{D(ON)}$	Turn-On Delay Time	V_{DD}=75V I_D=1A V_{GS}=10V R_{GEN}= 6 ohm		100		ns
t_r	Rise Time			58		ns
$t_{D(OFF)}$	Turn-Off Delay Time			225		ns
t_f	Fall Time			24		ns
Q_g	Total Gate Charge	V_{DS}=75V,I_D=10A,V_{GS}=10V		76		nC
Q_{gs}	Gate-Source Charge	V_{DS}=75V,I_D=10A, V_{GS}=10V		11		nC
Q_{gd}	Gate-Drain Charge			22		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=5A		0.8	1.3	V

Notes

a.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
b.Guaranteed by design, not subject to production testing.
c.Starting T_J=25°C,L=0.01mH,V_{DD} = 20V.(See Figure13)

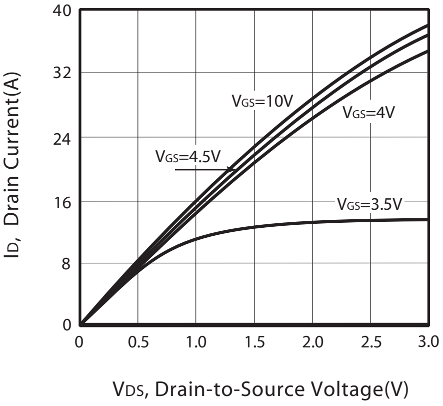


Figure 1. Output Characteristics

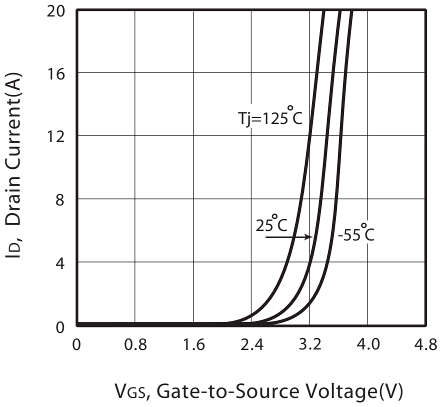


Figure 2. Transfer Characteristics

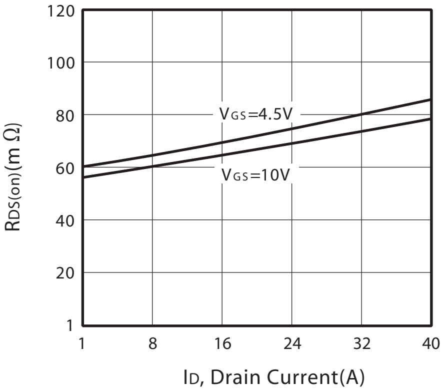


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

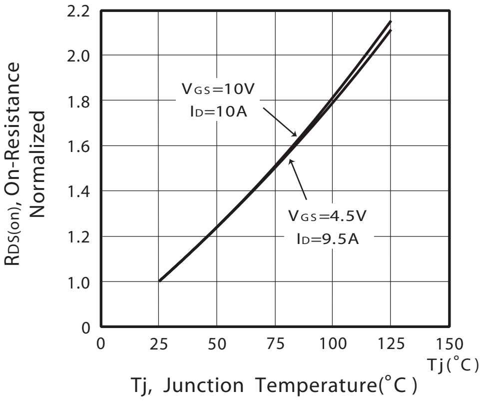


Figure 4. On-Resistance Variation with Drain Current and Temperature

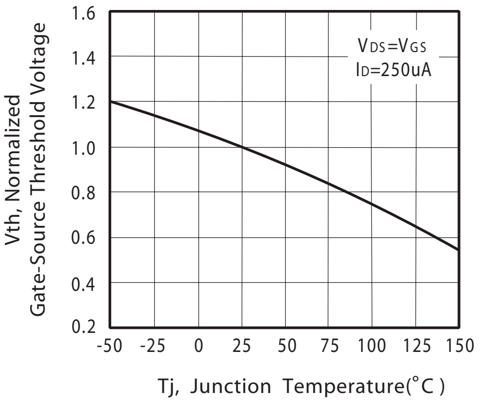


Figure 5. Gate Threshold Variation with Temperature

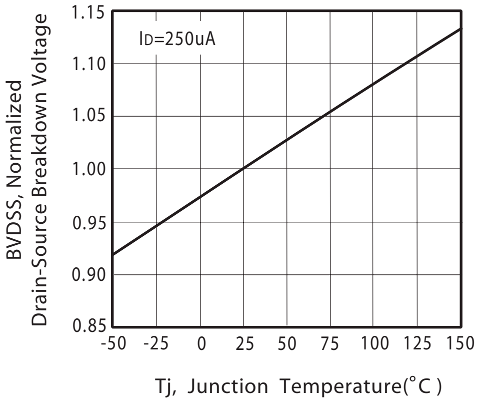


Figure 6. Breakdown Voltage Variation with Temperature

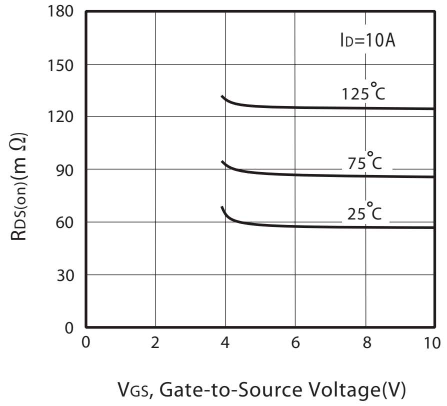


Figure 7. On-Resistance vs.
Gate-Source Voltage

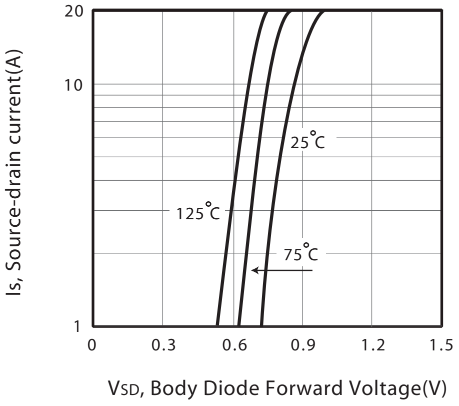


Figure 8. Body Diode Forward Voltage
Variation with Source Current

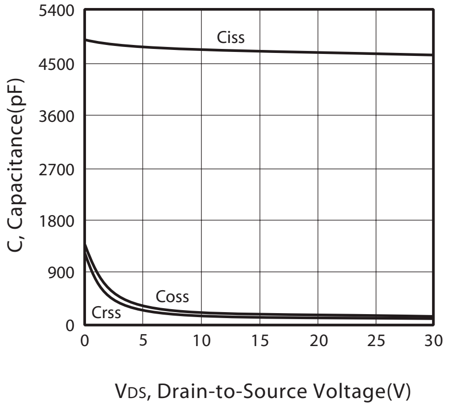


Figure 9. Capacitance

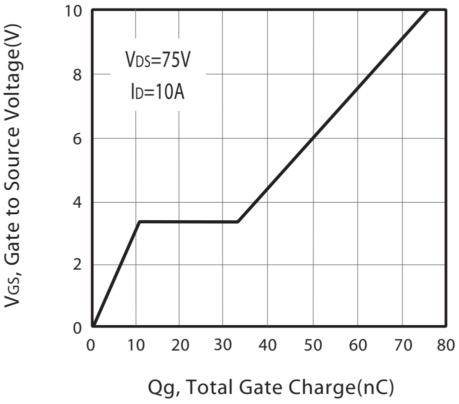


Figure 10. Gate Charge

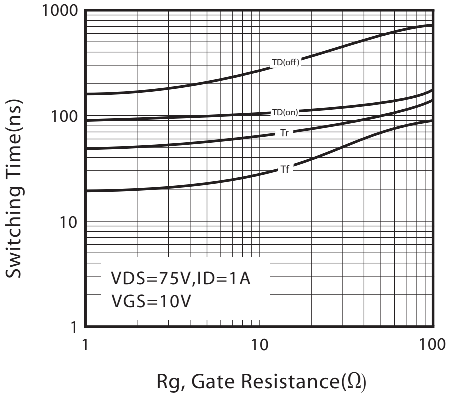


Figure 11. switching characteristics

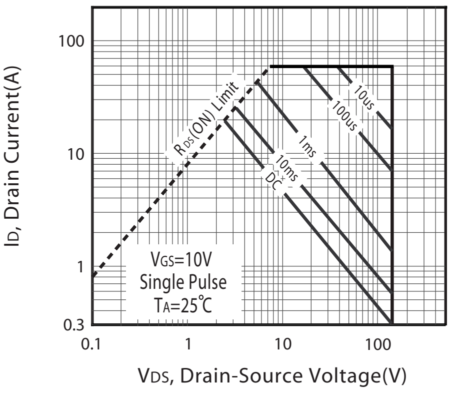
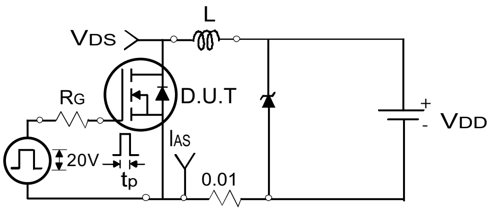
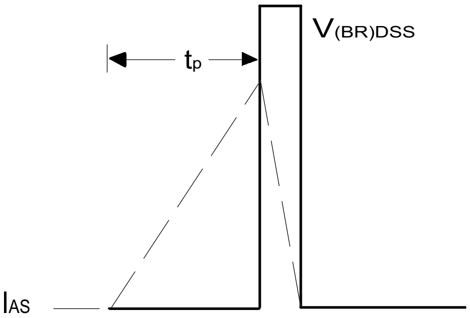


Figure 12. Maximum Safe Operating Area



Uncamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

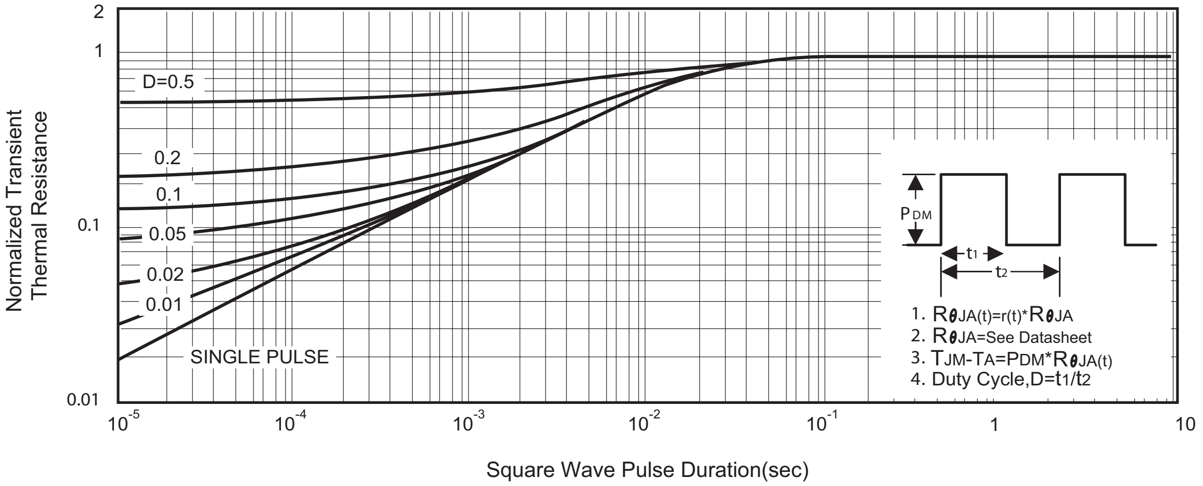
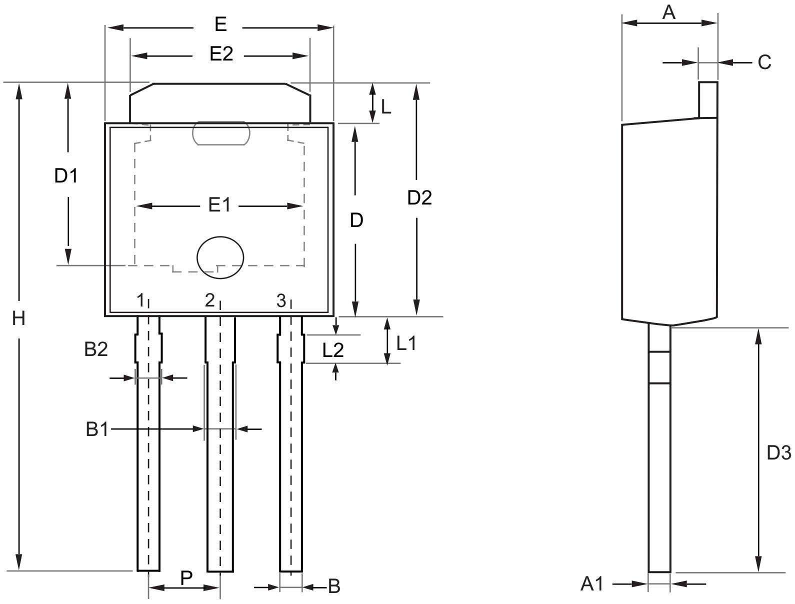


Figure 14. Normalized Thermal Transient Impedance Curve

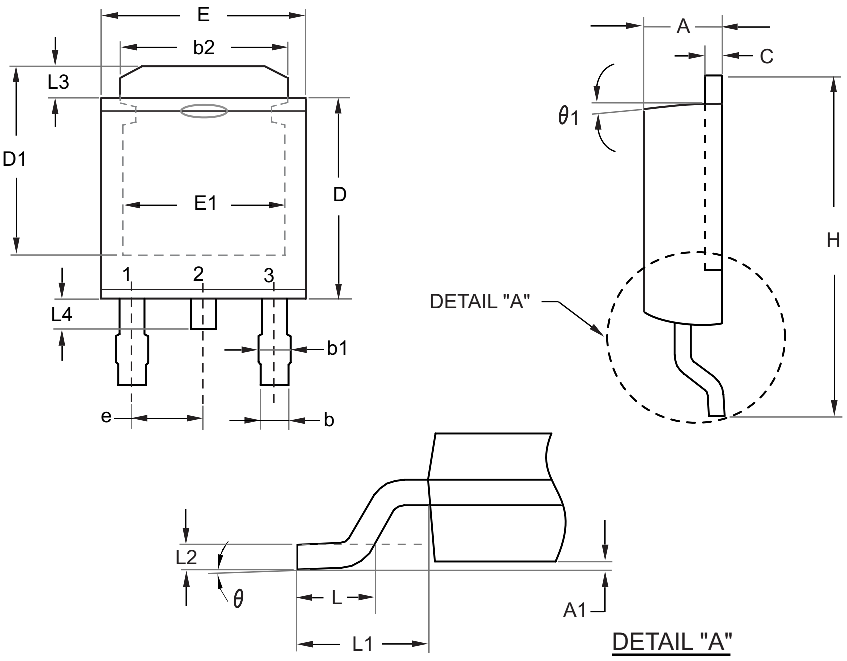
PACKAGE OUTLINE DIMENSIONS

TO-251



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.350	0.650	0.014	0.026
B	0.400	0.800	0.016	0.031
B1	0.650	1.050	0.026	0.041
B2	0.500	0.900	0.020	0.035
C	0.400	0.600	0.016	0.024
D	5.300	5.700	0.209	0.224
D1	4.900	5.300	0.193	0.209
D2	6.700	7.300	0.264	0.287
D3	7.000	8.000	0.276	0.315
H	13.700	15.300	0.539	0.602
E	6.300	6.700	0.248	0.264
E1	4.600	4.900	0.181	0.193
E2	4.800	5.200	0.189	0.205
L	1.300	1.700	0.051	0.067
L1	1.400	1.800	0.055	0.071
L2	0.500	0.900	0.020	0.035
P	2.300 BSC		0.091 BSC	

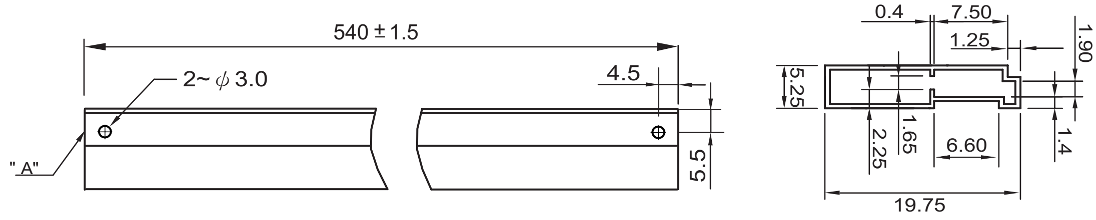
TO-252



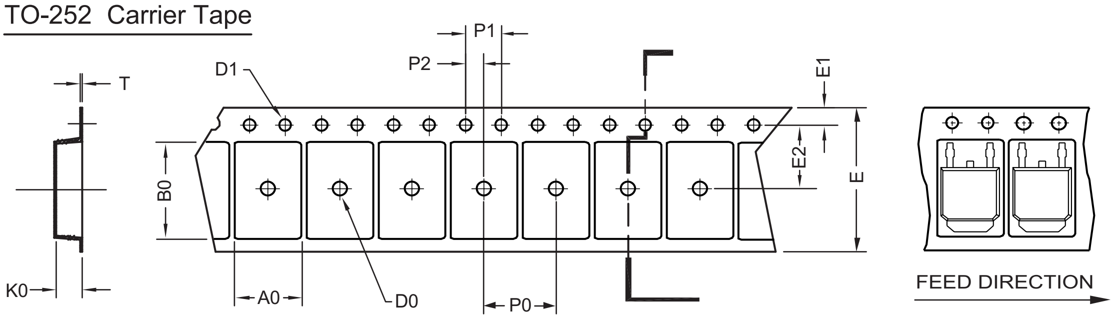
SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.000	0.200	0.000	0.008
b	0.400	0.889	0.016	0.035
b1	0.770	1.140	0.030	0.045
b2	4.800	5.460	0.189	0.215
C	0.400	0.600	0.016	0.024
D	5.300	6.223	0.209	0.245
D1	4.900	5.515	0.193	0.217
E	6.300	6.731	0.248	0.265
E1	4.320	5.004	0.170	0.197
e	2.290 REF		0.090 BSC	
H	8.900	10.400	0.350	0.409
L	1.397	1.780	0.055	0.070
L1	2.743 REF.		0.108 REF.	
L2	0.508 REF.		0.020 REF.	
L3	0.890	1.700	0.035	0.067
L4	0.500	1.100	0.020	0.043
θ	0°	10°	0°	10°
θ1	0°	15°	0°	15°

TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



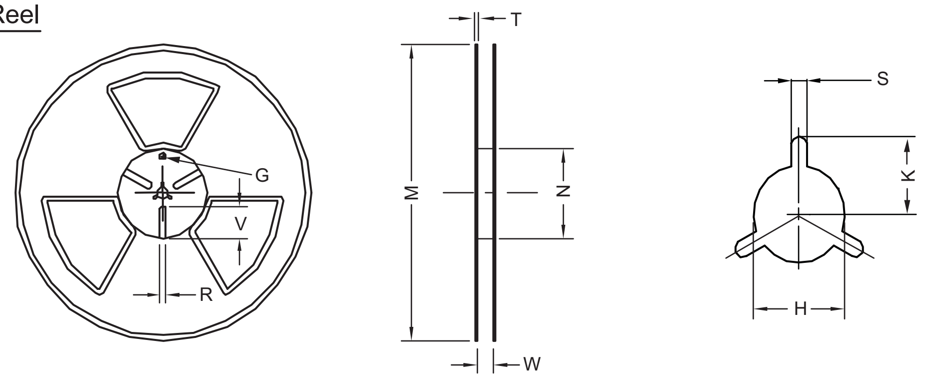
TO-252 Carrier Tape



UNIT:㎜

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 ㎜)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	ϕ 2	ϕ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:㎜

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 ㎜	ϕ 330	ϕ 330 ± 0.5	ϕ 97 ± 1.0	17.0 + 1.5 - 0	2.2	ϕ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---